





S3D20065A/S3D20065H/S3D20065G 650V SIC POWER SCHOTTKY RECTIFIERS

Description

S3D20065A/S3D20065H/S3D20065G are SiC Schottky rectifiers packaged in TO-220AC(TO-220-2)/TO-247AC(TO-247-2)/D2PAK(TO-263-2) case. The devices are high voltage Schottky rectifiers that have very low total conduction losses and very stable switching characteristics over temperature extremes. The S3D20065A/S3D20065H/S3D20065G are ideal for energy sensitive, high frequency applications in challenging

Features

- 175°C T_J operation
- Ultra-low switching loss
- Switching speeds independent of operating temperature
- Low total conduction losses
- · High forward surge current capability
- High package isolation voltage
- Terminals finish: 100% Pure Tin
- Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request

Applications

- Alternative energy inverters
- Power Factor Correction (PFC)
- Free-Wheeling diodes
- Switching supply output rectification
- · Reverse polarity protection

S3D20065A	S3D20065H	S3D20065G
1 2 K	1	K 2
TO-220AC	TO-247AC	D2PAK
(TO-220-2)	(TO-247-2)	(TO-263-2)
	1, K Cathode 2. Anode	



RoHS (P6)



Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	650	V
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @Tc=150°C, rectangular wave form	20	Α
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	10ms, Half Sine pulse, T _J =25°C	160	Α
Repetitive Peak Forward Surge Current	I_{FRM}	10 ms, Half Sine pulse , TJ =25°C	85	А

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V _{F1}	@ 20A, Pulse, T _J = 25 °C	1.5	1.7	V
	V_{F2}	@ 20A, Pulse, T _J = 175 °C	2.0	2.4	V
Reverse Current at DC condition*	I _{R1}	$@V_R = \text{rated } V_R$ $T_J = 25 ^{\circ}\text{C}$	0.03	30	uA
Reverse Current *	I _{R2}	$@V_R = \text{rated } V_R$ $T_J = 175 ^{\circ}\text{C}$	0.6	50	uA
Junction Capacitance	Ст	VR=0V, Tj=25℃,f=1MHz	1450	-	pF

^{*} Pulse width < 300 μ s, duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	S3D20065A	S3D20065H	S3D20065G	Units
Junction Temperature	TJ		-55 to +175		°C
Storage Temperature	T _{stg}	-55 to +175			°C
Typical Thermal Resistance Junction to Case	R ₀ JC	1.7	0.61	1.65	°C/W

Ordering Information

Device	Package	Plating	Shipping
S3D20065A	TO-220AC(TO-220-2)	Pure Sn	50pcs / tube
S3D20065H	TO-247AC(TO-247-2)	Pure Sn	25pcs / tube
S3D20065G	D2PAK(TO-263-2)	Pure Sn	800pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

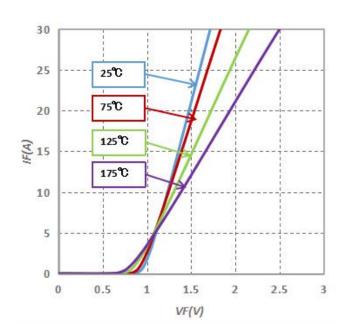
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Ratings and Characteristics Curves



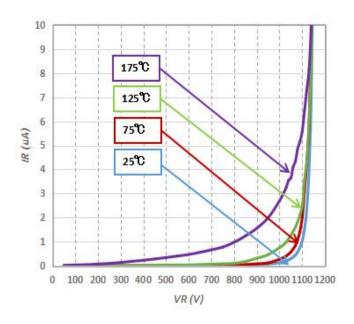


Fig.1-Typical Forward Voltage Characteristics



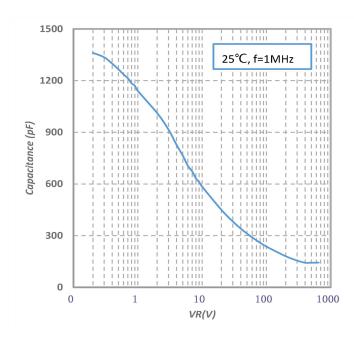


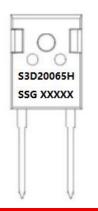
Fig.3-Capacitance vs. Reverse Voltage

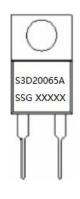


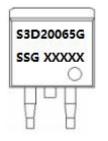




Marking Diagram







Where XXXXX is YYWWL

S3D = Device Type
A/H/G = Package type
20 = Forward Current ()

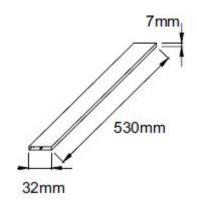
20 = Forward Current (20A) 065 = Reverse Voltage (650V) SSG = SSG

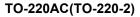
SSG = SSG YY = Year WW = Week L = Lot Number

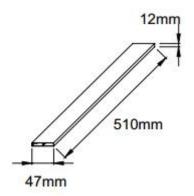
Cautions: Molding resin

Epoxy resin UL:94V-0

Tube Specification

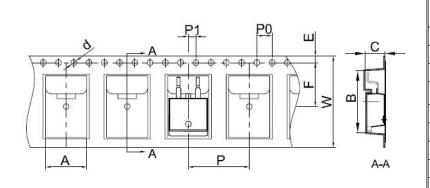






TO-247AC(TO-247-2)

Carrier Tape & Reel Specification D2PAK(TO-263-2)



SYMBOL	Millimeters		
STWIBOL	Min.	Max.	
Α	10.70	10.90	
В	16.03	16.23	
С	5.11	5.31	
d	1.45	1.65	
E	1.65	1.85	
F	11.40	11.60	
P0	3.90	4.10	
Р	15.90	16.10	
P1	1.90	2.10	
W	23.90	24.30	

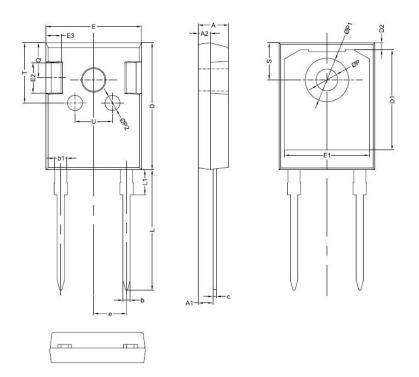
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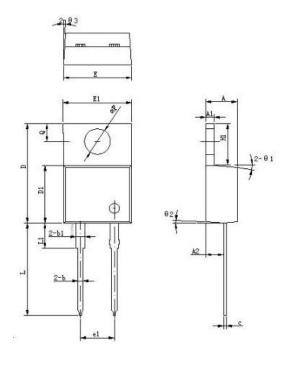


Mechanical Dimensions TO-247AC(TO-247-2)



SYMBOL	Millimeters			
	MIN.	TYP.	MAX.	
Α	4.80	5.00	5.20	
A1	2.20	2.41	2.61	
A2	1.90	2.00	2.10	
b	1.10	1.20	1.35	
b1	1.80	2.00	2.20	
С	0.50	0.60	0.75	
D	20.30	21.00	21.20	
D1		16.58		
D2 E		1.17		
E	15.60	15.80	16.00	
E1		14.02		
E2		5.00		
E3		2.50		
e		5.44		
L	19.42	19.92	20.42	
L1		4.13		
Р	3.50	3.60	3.70	
P1	7.1	7.19	7.40	
P2		2.50		
Q		5.80		
P2 Q S T	6.05	6.15	6.25	
Т		10.00	_	
U		6.20		

Mechanical Dimensions TO-220AC(TO-220-2)



Symbol	Dimensions in millimeters			
- Cymber	Min.	Typical	Max.	
Α	4.55	4.70	4.85	
A1	1.17	1.27	1.37	
A2	2.59	2.69	2.89	
b	0.71	0.81	0.96	
b1		1.27		
С	0.36	0.38	0.61	
D	14.64	14.94	15.24	
D1	8.55	8.70	8.90	
E	10.01	10.16	10.31	
E1	9.98	10.18	10.38	
e1		5.08		
H1	6.04	6.24	6.44	
L	13.00	13.86	14.08	
L1		3.80		
ФР	3.74	3.84	4.04	
Q	2.54	2.74	2.94	
Θ1		5°		
Θ2		4°		
Θ3		4°	<u> </u>	

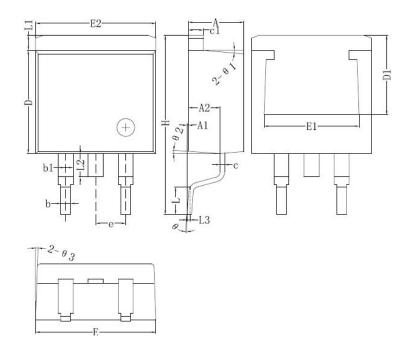
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Mechanical Dimensions D²PAK(TO-263-2)



	Dimensions in millimeters			
Symbol	Min.	Typical	Max.	
Α	4.55	4.70	4.85	
A1	0	0.10	0.25	
A2	2.59	2.69	2.89	
b	0.71	0.81	0.96	
b1		1.27		
С	0.36	0.38	0.61	
c1	1.17	1.27	1.37	
D	8.55	8.70	8.85	
D1	6.40			
E	10.01	10.16	10.31	
E1	7.6			
E2	9.98	10.08	10.18	
е		2.54		
Н	14.6	15.1	15.6	
L	2.00	2.30	2.70	
L1	1.17	1.27	1.40	
L2			2.20	
L3		0.25BSC		
Θ	0	-	8°	
Θ1		5°		
Θ2		4°		
Θ3		4°		







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